

**Silicon PNP Power Transistor**

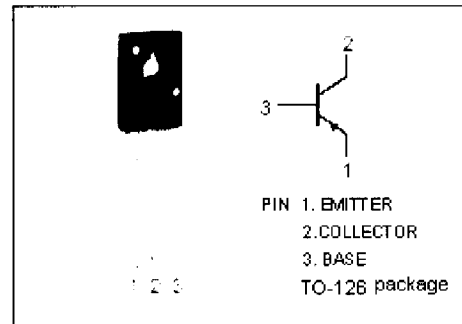
**2SA1217**

**DESCRIPTION**

- Collector-Emitter Breakdown Voltage-  
 $V_{(BR)CEO} = -40V$  (Min)
- Good Linearity of  $h_{FE}$
- Complement to Type 2SC2877

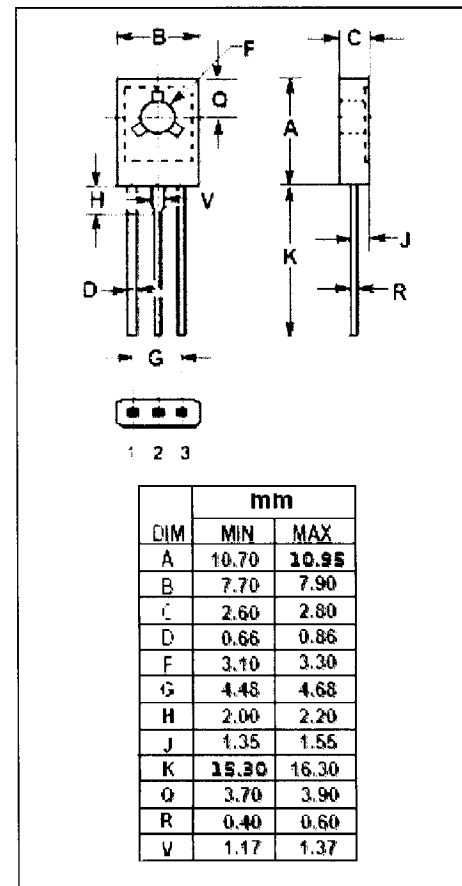
**APPLICATIONS**

- Designed for audio frequency power amplifier and low speed switching applications.
- Suitable for output stage of 5 watts car radio and car stereo.

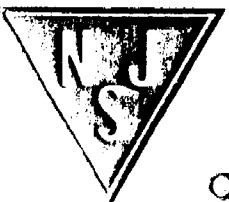


**ABSOLUTE MAXIMUM RATINGS(Ta=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-40	V
$V_{CEO}$	Collector-Emitter Voltage	-40	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-3	A
$I_B$	Base Current-Continuous	-1	A
$P_C$	Total Power Dissipation @ $T_C=25^\circ C$	10	W
$T_J$	Junction Temperature	150	°C
$T_{stg}$	Storage Temperature Range	-55~150	°C



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## 2SA1217

### ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}; I_B = 0$	-40			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -2\text{A}; I_B = -0.2\text{A}$			-0.8	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -0.5\text{A}; V_{CE} = -2\text{V}$			-1.0	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -40\text{V}; I_E = 0$			-0.1	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-0.1	$\mu\text{A}$
$h_{FE-1}$	DC Current Gain	$I_C = -0.5\text{A}; V_{CE} = -2\text{V}$	80		240	
$h_{FE-2}$	DC Current Gain	$I_C = -2.5\text{A}; V_{CE} = -2\text{V}$	25			
$f_T$	Current-Gain—Bandwidth Product	$I_C = -0.5\text{A}; V_{CE} = -2\text{V}$		100		MHz
$C_{OB}$	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f = 1.0\text{MHz}$		35		pF

#### ◆ $h_{FE}$ Classifications

O	Y
80-160	120-240